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Atty. Docket No. 04329.2222		Serial No.	Not Yet Assigned		
Applicant Kouji MATSUO et al.					
Filing Date January 28, 2000		Group			
U.S. PATENT DOCUMENTS					
Examiner Initial*	Document Number	Date	Name	Class	Sub Class
FOREIGN PATENT DOCUMENTS					
	Document Number	Date	Country	Class	Sub Class
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
<i>CW</i>	Wittner, M. et al. "Oxidation Kinetics of TiN Thin Films", J. Appl. Phys., Vol. 52, pp. 6659-6664, November (1981).				
<i>SN</i>	Matsuo, K. et al., "Reliable High-k TiO ₂ Gate Insulator Formed by Ultrathin TiN Deposition and Low Temperature Oxidation", Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials pp. 164-165, (1999).				
Examiner <i>J</i>	Date Considered 15/16/01				
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